

No.C933B

2SK334



Silicon N-Channel Junction-Type Field Effect TR
FOR CONDENSER MICROPHONES

## FEATURE

Because it has an ultra-compact outline, sets can be made compact.

ABSOLUTE MAXIMUM RATINGS/	Ta = 25°C		unit
Drain-gate current	VDGO	-20	V
Gate current	IG	10	mA
Allowable power dissipation	PD	100	mW
Junction temperature	Tj	125	*C
Storage ambient temperature	Teta	_40 ~ +125	°C

ELECTRICAL CHARACTERISTICS/T<sub>R</sub> = 25°C min typ max unit

Drain current IDSS\* VDS = 10 V, VGS = 0V 60\* 800\* μΑ

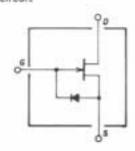
[Ta = 25°C, VCC = 4.5 V, RD = 680 Ω, Cin = 15 pF, in a specified test circuit (conforming with application circuit)].

			min	typ	max	unit
Transmission loss	Gv			-5		dB
Transmission loss voltage-drop characteristics	$\Delta G_{\Psi}V$	V <sub>CC</sub> = 4.5 ~ 1.5 V, f = 1 kHz v <sub>i</sub> = 10 mV			-3	dB
Transmission loss frequency characteristics	$\Delta G_{Vf}$	$f=1~k\sim 110~Hz, v_i=10~mV$			-1	dB
Input impedance	zi	f = 1 kHz	20			MΩ
Output noise voltage	VNO	vi = 0, A-curve			-110	dB

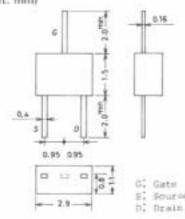
\* 2SK334 is graded as follows by drain current IDSS: (unit: mm)

	60	N11	180	150	N12	300	250	N13	450	400	N14	800	
н							1000000			pr 2/G+1/2	100	11.70	

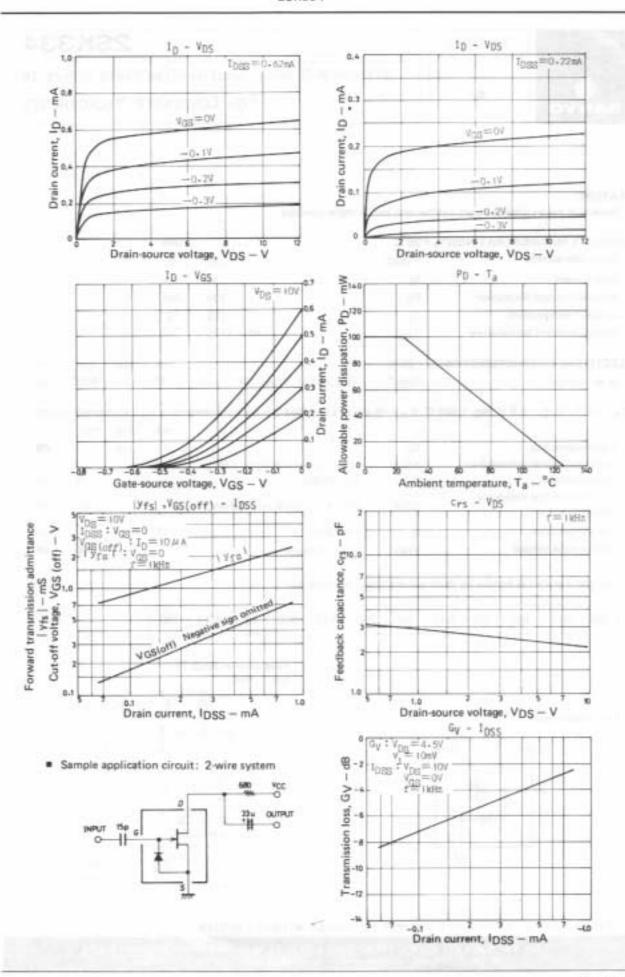
Equivalent circuit

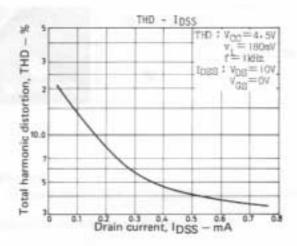


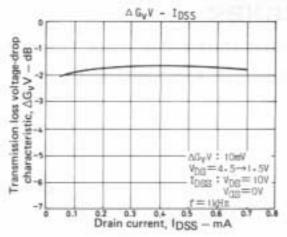
Case Outline 2025-TR (unit: mm)



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